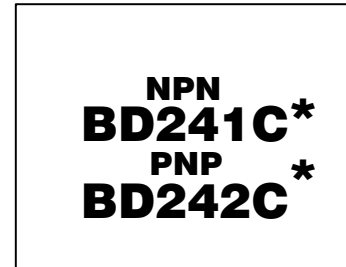


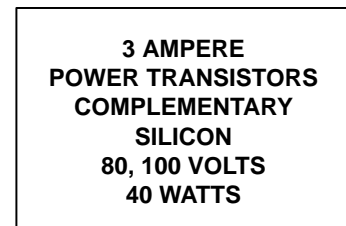
Complementary Silicon Plastic Power Transistors

... designed for use in general purpose amplifier and switching applications.

- Collector–Emitter Saturation Voltage —
 $V_{CE} = 1.2 \text{ Vdc (Max) @ } I_C = 3.0 \text{ Adc}$
- Collector–Emitter Sustaining Voltage —
 $V_{CEO(sus)} = 100 \text{ Vdc (Min.) BD241C, BD242C}$
- High Current Gain — Bandwidth Product
 $f_T = 3.0 \text{ MHz (Min) @ } I_C = 500 \text{ mAdc}$
- Compact TO–220 AB Package

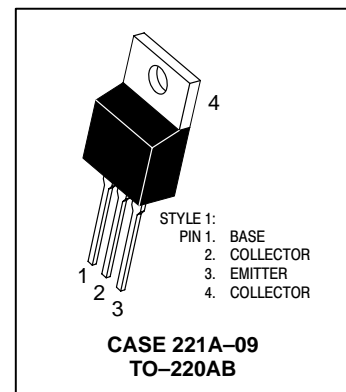


*ON Semiconductor Preferred Device



MAXIMUM RATINGS

Rating	Symbol	BD241C BD242C	Unit
Collector–Emitter Voltage	V_{CEO}	100	Vdc
Collector–Emitter Voltage	V_{CES}	115	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current — Continuous Peak	I_C	3.0 5.0	Adc Adc
Base Current	I_B	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.125	$^\circ\text{C/W}$

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

BD241C BD242C

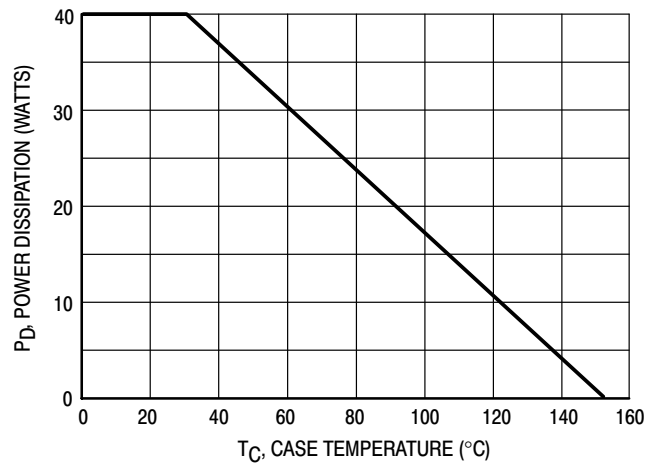


Figure 1. Power Derating

BD241C BD242C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ¹ ($I_C = 30\text{ mAdc}$, $I_B = 0$)	BD241C, BD242C	V_{CEO}	100	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	BD241C, BD242C	I_{CEO}	0.3	mAdc
Collector Cutoff Current ($V_{CE} = 100\text{ Vdc}$, $V_{EB} = 0$)	BD241C, BD242C	I_{CES}	200	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	1.0	mAdc
ON CHARACTERISTICS¹				
DC Current Gain ($I_C = 1.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)		h_{FE}	25 10	
Collector–Emitter Saturation Voltage ($I_C = 3.0\text{ Adc}$, $I_B = 600\text{ Adc}$)		$V_{CE(sat)}$	1.2	Vdc
Base–Emitter On Voltage ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)		$V_{BE(on)}$	1.8	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product ² ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 1\text{ MHz}$)		f_T	3.0	MHz
Small–Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1\text{ kHz}$)		h_{fe}	20	

¹ Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

² $f_T = |h_{fe}| \cdot f_{test}$.

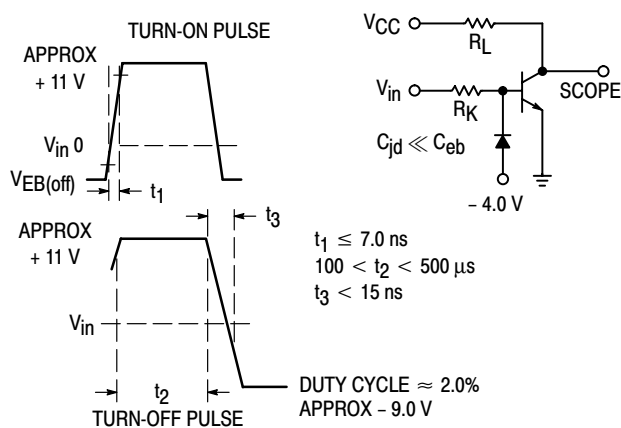


Figure 2. Switching Time Equivalent Circuit

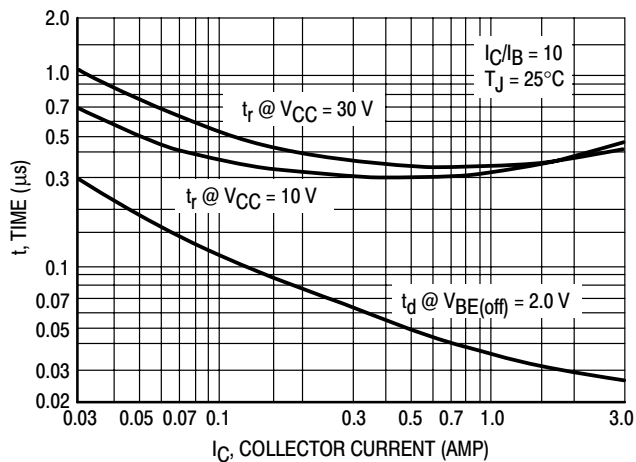


Figure 3. Turn–On Time

BD241C BD242C

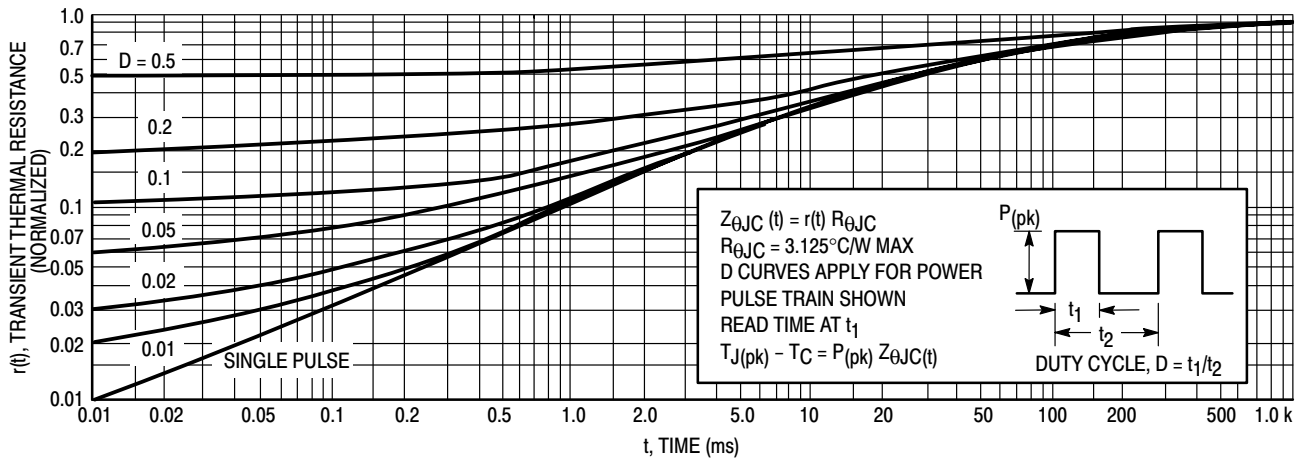


Figure 4. Thermal Response

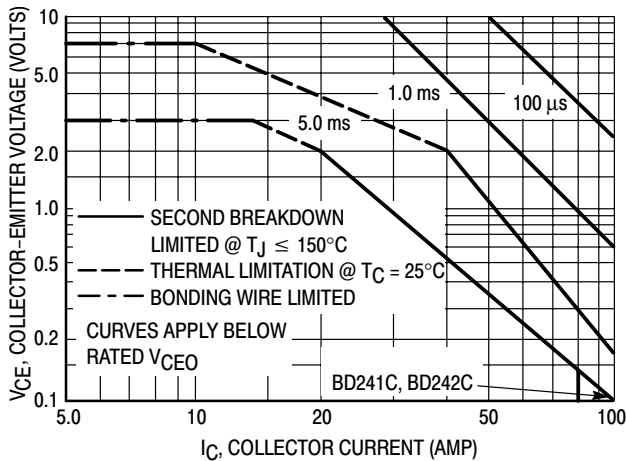


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

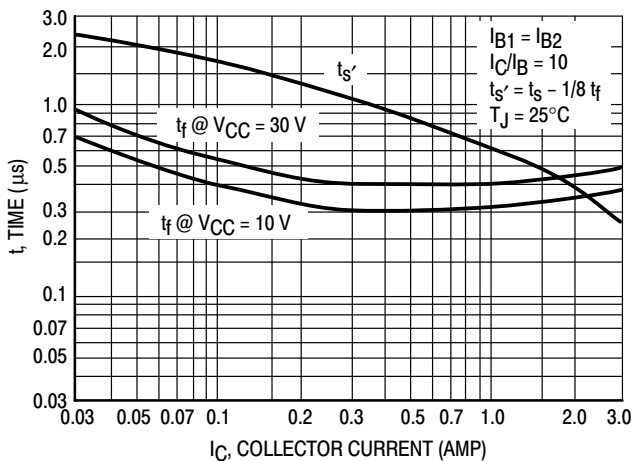


Figure 6. Turn-Off Time

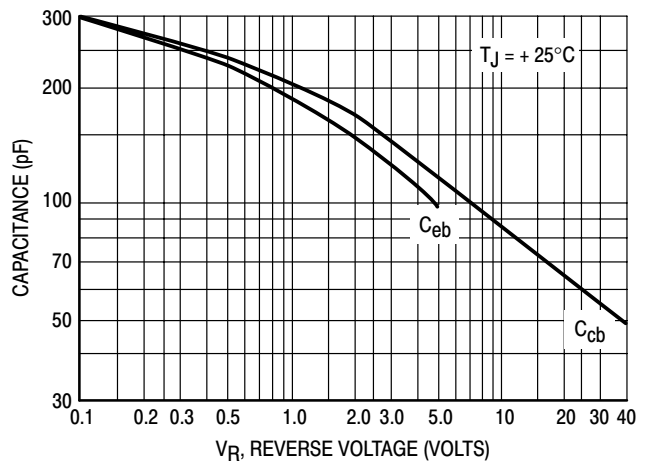


Figure 7. Capacitance

BD241C BD242C

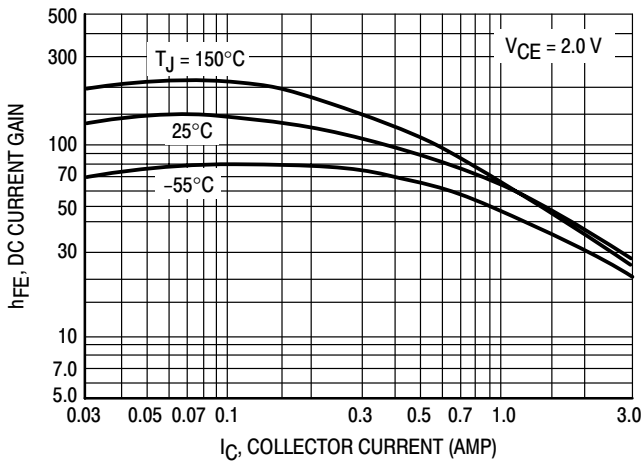


Figure 8. DC Current Gain

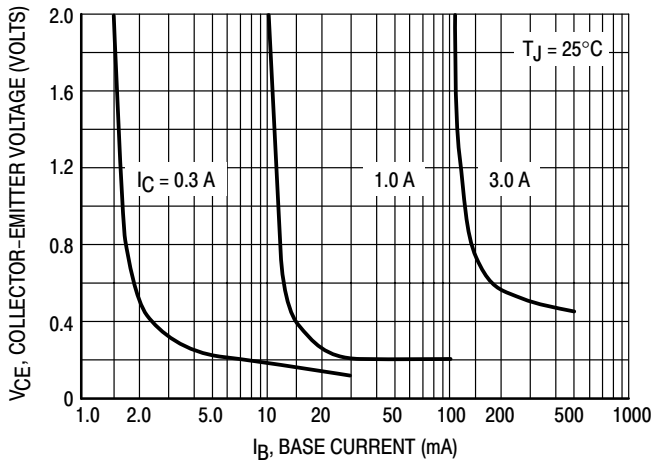


Figure 9. Collector Saturation Region

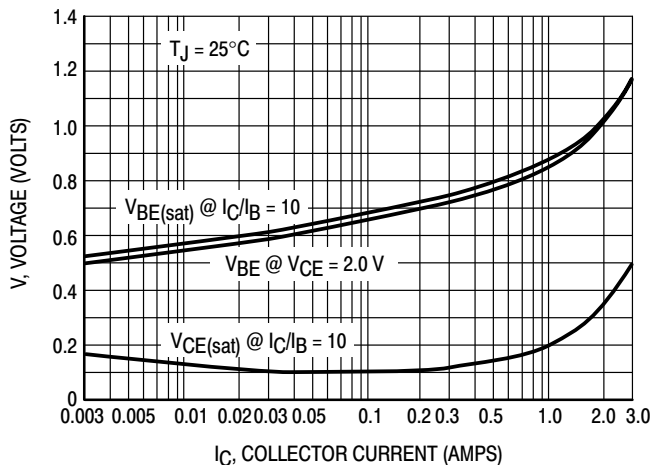


Figure 10. "On" Voltages

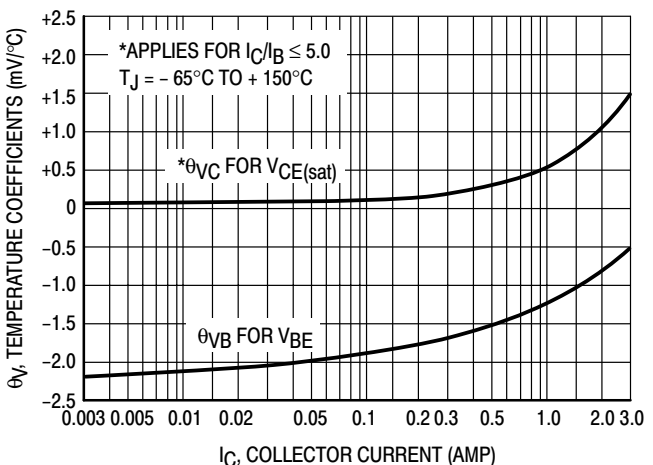


Figure 11. Temperature Coefficients

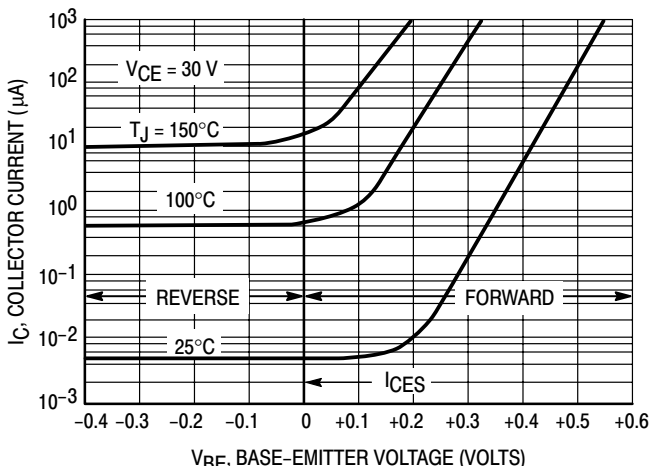


Figure 12. Collector Cut-Off Region

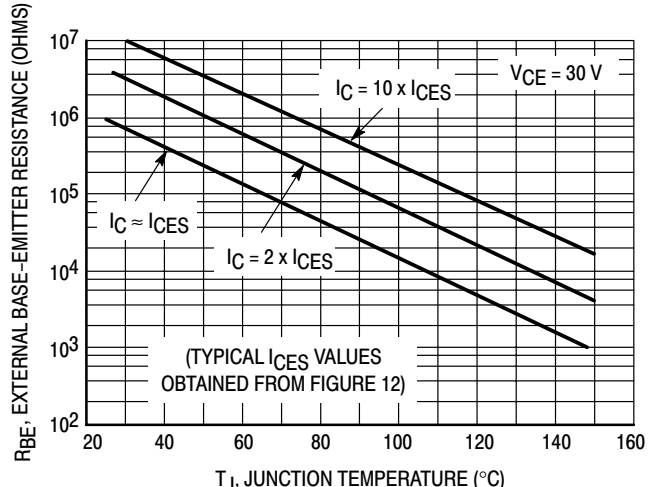
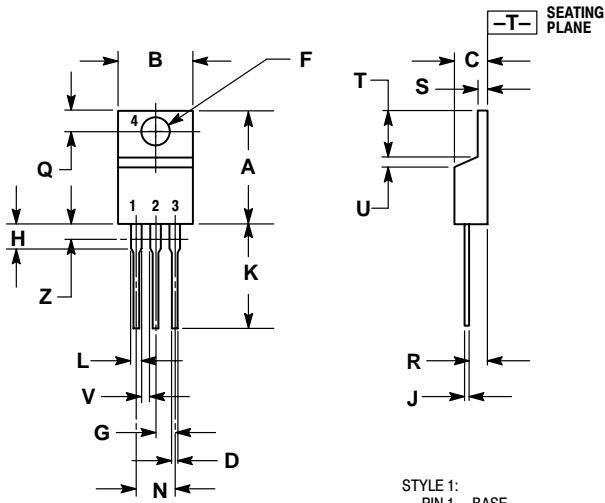


Figure 13. Effects of Base-Emitter Resistance

BD241C BD242C

PACKAGE DIMENSIONS

TO-220AB CASE 221A-09 ISSUE AB




STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

Notes

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